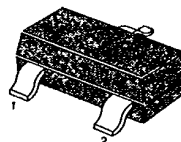


MMBT4125**PNP EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CE0}	30	V
Emitter-Base Voltage	V_{EB0}	4	V
Collector Current	I_C	200	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBT 3906 for graphs

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1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 10\mu\text{A}$, $I_E = 0$	30		V
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = 1\text{mA}$, $I_E = 0$	30		V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = 10\mu\text{A}$, $I_C = 0$	4		V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 20\text{V}$, $I_E = 0$		50	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 3\text{V}$, $I_C = 0$		50	nA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 2.0\text{mA}$	50	150	
		$V_{CE} = 1\text{V}$, $I_C = 50\text{mA}$	25		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}$, $I_B = 5.0\text{mA}$		0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}$, $I_B = 5.0\text{mA}$		0.95	V
Current Gain-Bandwidth Product	f_T	$I_C = 10\text{mA}$, $V_{CE} = 20\text{V}$ $f = 100\text{MHz}$	200		MHz
Collector Base Capacitance	C_{cb}	$V_{CB} = 5\text{V}$, $I_E = 0$ $f = 100\text{KHz}$		4.5	pF
Noise Figure	NF	$I_C = 100\mu\text{A}$, $V_{CE} = 5\text{V}$ $R_S = 1\text{K}\Omega$, $f = 10\text{Hz to } 15.7\text{KHz}$		5	dB

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Marking



SAMSUNG SEMICONDUCTOR

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